Formation of Required Typeness InSb By Crystal Ion Slicing

Damien Johnson and Pradeep Bhattacharya

Electrical Engineering Department
Southern University

Abstract

A usual p-n junction has a p-type and n-type monolithic structure. For example, n-type Indium Antimonide (InSb) can carry currents in the form of electrons with a negative charge and a p-type Indium Antimonide can carry currents in the form of electrons with a positive charge. During this process, a pn junction is formed, causing electrons to diffuse into the p-layer and holes to diffuse into the p-layer. A depletion region is formed when an electromotive force is caused and charges are swept to the appropriate layer.

DAMIEN JOHNSON
Damien Johnson is a senior majoring in electrical engineering at Southern University of Baton Rouge. He has been conducting research with Dr. Pradeep Bhattacharya for four years as his mentee. Email: damien_johnson@yahoo.com

PRADEEP BHATTACHARYA
Dr. Pradeep Bhattacharya is the interm-chairman for the Department of Electrical Engineering and a professor of electronics at Southern University of Baton Rouge. Email: bhattach@engr.subr.edu

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